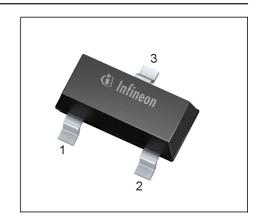


Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 1 mA to 20 mA
- f_T = 8 GHz, NF_{min} = 0.9 dB at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BFR182	RGs	1=B	2=E	3=C	SOT23

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{\sf CEO}$	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I _C	35	mA
Base current	I_{B}	4	
Total power dissipation ¹⁾	P _{tot}	250	mW
<i>T</i> _S ≤ 93 °C			
Junction temperature	T_{J}	150	°C
Ambient temperature	T _A	-65 150	
Storage temperature	T_{Stq}	-65 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	230	K/W

 $^{^1}T_{
m S}$ is measured on the collector lead at the soldering point to the pcb

²For the definition of $R_{th,JS}$ please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Symbol		Values	
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V _{(BR)CEO}	12	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0	, ,				
Collector-emitter cutoff current	I _{CES}	-	-	100	μΑ
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I_{CBO}	-	-	100	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	1	μΑ
$V_{\rm EB} = 1 \text{ V}, I_{\rm C} = 0$					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, pulse measured					



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

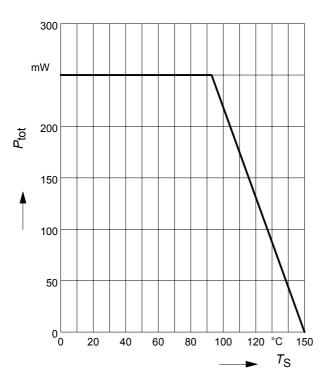
Parameter	Symbol		Values		
			typ.	max.	
AC Characteristics (verified by random sampling	ng)				
Transition frequency	f _T	6	8	-	GHz
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.32	0.5	pF
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,					
emitter grounded					
Collector emitter capacitance	C_{ce}	-	0.2	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	0.8	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,					
collector grounded					
Minimum noise figure	NF _{min}				dB
$I_{\rm C}$ = 3 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 900 MHz		-	0.9	-	
$I_{\rm C}$ = 3 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 1.8 GHz		-	1.3	-	
Power gain, maximum available ¹⁾	G _{ma}				
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 900 MHz		-	18	-	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 1.8 GHz		-	12	-	
Transducer gain	$ S_{21e} ^2$				dB
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		-	15	-	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 GHz		-	9.5	-	

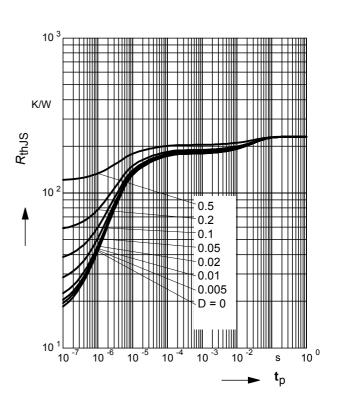
 $^{^{1}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$



Total power dissipation $P_{tot} = f(T_S)$

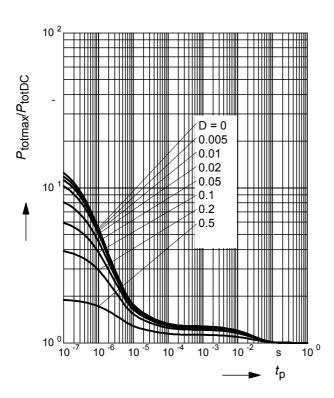
Permissible Pulse Load $R_{thJS} = f(t_p)$





Permissible Pulse Load

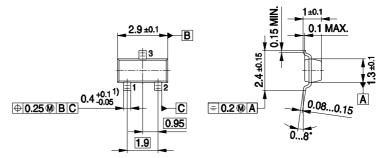
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$$





Package Outline

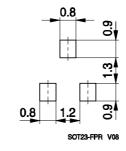




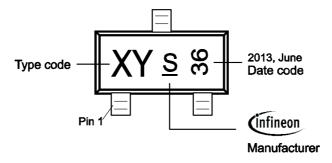
1) Lead width can be 0.6 max. in dambar area

SOT23-PO V08

Foot Print

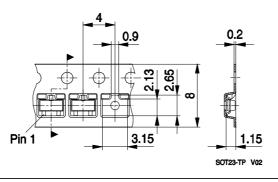


Marking Layout



Standard Packing

Reel o 180 mm: 3.000 Pieces / Reel Reel o 330 mm = 10.000 Pieces / Reel





Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

© 2009 Infineon Technologies AG All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Bipolar Transistors category:

Click to view products by Infineon manufacturer:

Other Similar products are found below:

MAPRST0912-50 MCH4016-TL-H MMBT5551-G MRF10120 15GN01CA-TB-E PH1214-25M MAPRST0912-350 MMBTH10-TP BFP 640F H6327 BFR 360F H6765 MRF10031 NSVF4009SG4T1G BFP 182R E7764 BFP405H6740XTSA1 MRF10350 ASMA201 BFR360FH6765XTSA1 BFP410H6327XTSA1 BFP620FH7764XTSA1 BFP720ESDH6327XTSA1 BFP720FH6327XTSA1 BFP720FH6327XTSA1 BFP720FH6327XTSA1 BFP720FH6327XTSA1 BFP720FH6327XTSA1 BFP720FH6327XTSA1 BFP720FH6327XTSA1 MMBT2222A-G BFP196WH6327XTSA1 BFP405FH6327XTSA1 BFP640ESDH6327XTSA1 BFR193L3E6327XTMA1 BFS483H6327XTSA1 NSVF4020SG4T1G NSVF6003SB6T1G MRF10005 BFP420FH6327XTSA1 BFP740FESDH6327XTSA1 BFR181E6327HTSA1 BFR181WH6327XTSA1 BFR182E6327HTSA1 BFR193E6327HTSA1 BFP181E7764HTSA1 BFP183WH6327XTSA1 BFP720H6327XTSA1 BFR182WH6327XTSA1 BFP180F764HTSA1 BFP183WH6327XTSA1 BFP720H6327XTSA1 BFR182WH6327XTSA1 BFV590GX MAPR-000912-500S00 BFR340FH6327XTSA1 STGWT30HP65FB